

What is claimed is:

1. A flip-chip light-emitting device, comprising
a transparent substrate;
a semiconductor stacked structure arranged over a main surface of said transparent substrate wherein said stacked structure comprises an n-type GaN-based III-V Group compound semiconductor layer adjacent to said main surface and a p-type GaN-based III-V Group compound semiconductor layer adjacent to said n-type semiconductor layer;
a first electrode being in electrical contact with said n-type semiconductor layer; and
a second electrode being in electrical contact with said p-type semiconductor layer;
wherein said second electrode has good reflectivity of light and covers most of the outer surface of said p-type semiconductor layer.
2. The device of Claim 1 wherein said stacked structure further comprises an active layer placed between said n-type semiconductor layer and said p-type semiconductor layer.
3. The device of Claims 1 or 2 further comprising an insulating layer at least coated on the side surface of the stacked structure, a portion of said first electrode and a portion of said second electrode.
4. The device of Claims 1 or 2 further comprising a base which has a first and a second conductive portions respectively connected to said first and second electrodes.
5. The device of Claim 4 wherein said base can be a conductive lead frame, a glass lead frame, a circuit board or a thin-film circuit.
6. The device of Claims 1 or 2 wherein said second electrode is a multi-layer structure comprising a light-transmitting conductive layer and a layer of aluminium (Al) or silver (Ag).

7. The device of Claims 1 or 2 wherein said second electrode is a multi-layer structure of nickel gold titanium aluminium (Ni Au Ti Al), Indium-Tin Oxide aluminium (ITO Al) or Indium-Tin Oxide silver (ITO Ag).
8. A flip-chip light-emitting device, comprising:
 - a transparent substrate;
 - a semiconductor stacked structure arranged over a main surface of said transparent substrate wherein said stacked structure comprises an p-type GaN-based III-V Group compound semiconductor layer adjacent to said main surface and a n-type GaN-based III-V Group compound semiconductor layer adjacent to said p-type semiconductor layer;
 - a first electrode being in electrical contact with said n-type semiconductor layer; and
 - a second electrode being in electrical contact with said p-type semiconductor layer;wherein said first electrode has good reflectivity of light and covers most of the outer surface of said n-type semiconductor layer.
9. The device of Claim 8 wherein said stacked structure further comprises an active layer placed between said n-type semiconductor layer and the p-type semiconductor layer.
10. The device of Claims 8 or 9 further comprising an insulating layer at least coated on the side surface of the stacked structure, a portion of said first electrode and a portion of said second electrode.
11. The device of Claims 8 or 9 further comprising a base which has a first and a second conductive portions respectively connected to said first and second electrodes.
12. The device of Claim 11 wherein said base can be a conductive lead frame, a glass lead frame, a circuit board or a thin-film circuit.
13. The device of Claims 8 or 9 wherein said second electrode is a multi-layer

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structure comprising a light-transmitting conductive layer and a layer of aluminium (Al) or silver (Ag).

14. The device of Claims 8 or 9 wherein said second electrode is a multi-layer structure of titanium aluminium (Ti Al), titanium silver (Ti Ag), Indium-Tin Oxide aluminium (ITO Al) or Indium-Tin Oxide silver (ITO Ag).